



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

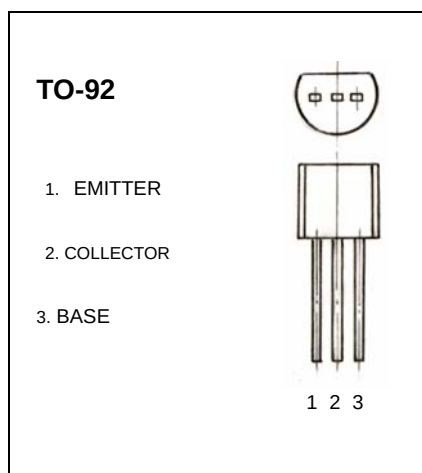
TO-92 Plastic-Encapsulate Transistors

B772 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 625 mW ($T_{amb}=25^{\circ}C$)



MAXIMUM RATINGS* $T_A=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Dissipation	0.625	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A$, $I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA$, $I_B=0$	-30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A$, $I_C=0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB}=-40V$, $I_E=0$			-1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-30V$, $I_B=0$			-10	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-6V$, $I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-2V$, $I_C=-1A$	60		400	
	$h_{FE(2)}$	$V_{CE}=-2V$, $I_C=-100mA$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A$, $I_B=-0.2A$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2A$, $I_B=-0.2A$			-1.5	V
Transition frequency	f_T	$V_{CE}=-5V$, $I_C=-0.1A$ $f=10MHz$	50			MHz

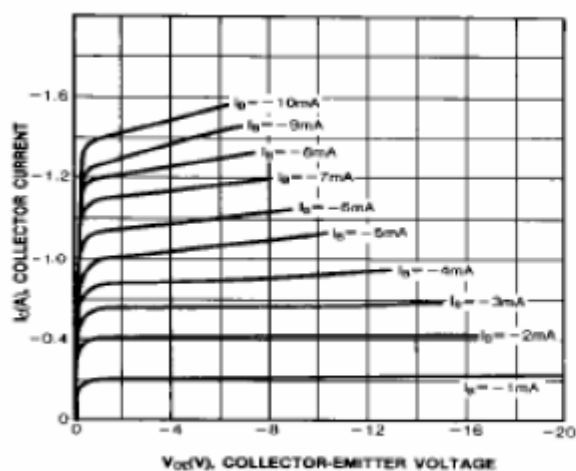
CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

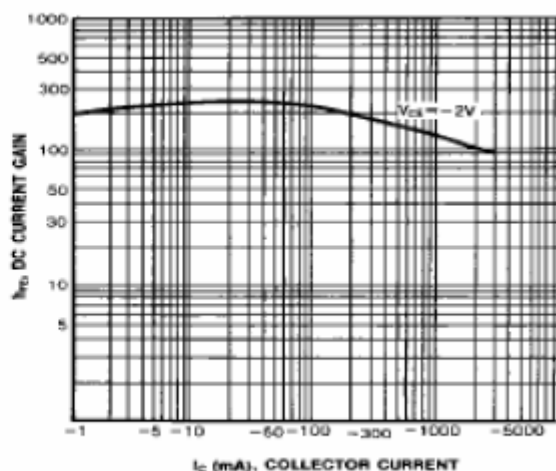
Typical characteristics

B772

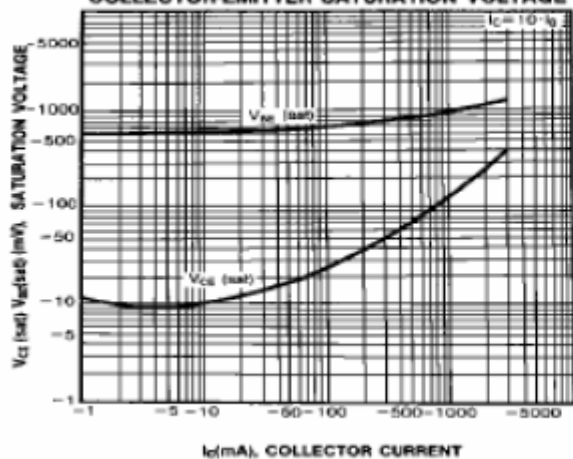
STATIC CHARACTERISTIC



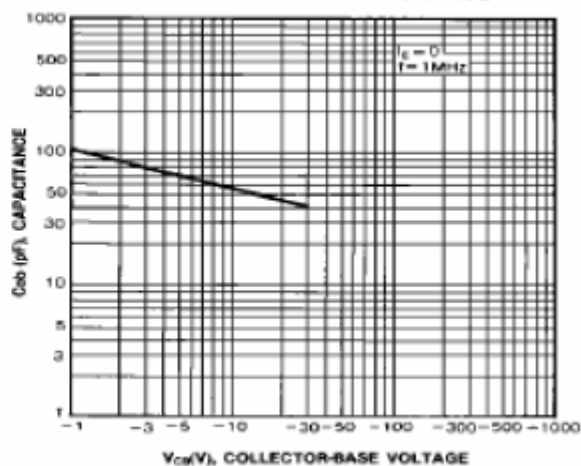
DC CURRENT GAIN



BASE-EMITTER SATURATION VOLTAGE
COLLECTOR-EMITTER SATURATION VOLTAGE



COLLECTOR OUTPUT CAPACITANCE



CURRENT GAIN-BANDWIDTH PRODUCT

